(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
7 November 2002 (07.11.2002)

PCT

(10) International Publication Number
WO 02/089182 A3

(51) International Patent Classification[7]: H01L 21/8242, 27/108

(21) International Application Number: PCT/US02/13196

(22) International Filing Date: 26 April 2002 (26.04.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/842,788 27 April 2001 (27.04.2001) US

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZM, ZW.

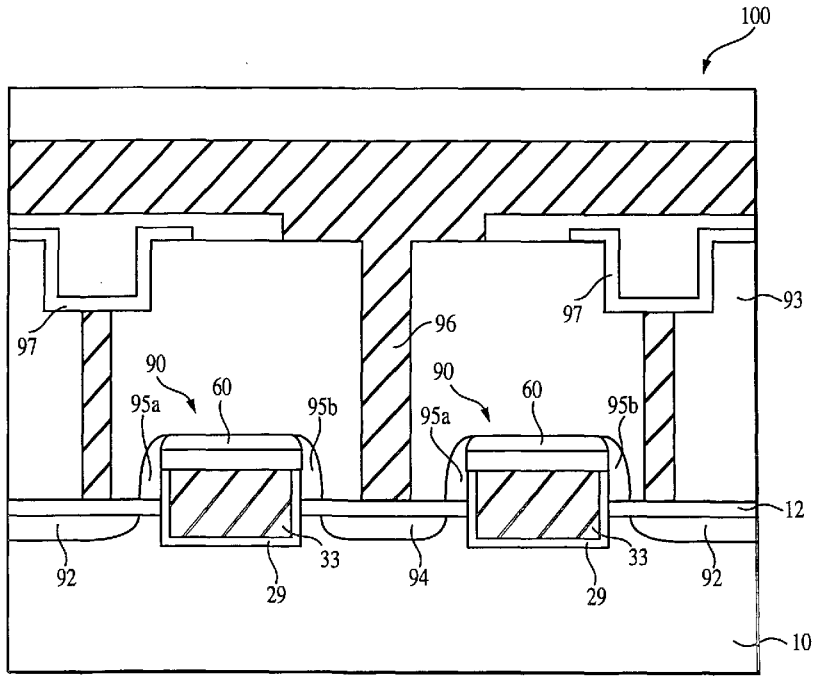
(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

(88) Date of publication of the international search report:
6 November 2003

[Continued on next page]

(54) Title: RECESSED GAT DRAM TRANSISTOR AND METHOD



(57) Abstract: A method of forming memory devices, such as DRAM access transistors, having recessed gate structures is disclosed. Field oxide area (21) for isolation are first formed over a semiconductor substrate subsequent to which transistor grooves (22) are patterned and etched in a silicon nitride layer (18). The field oxide areas adjacent to the transistor grooves are then recessed, so that subsequently deposited polysilicon for gate structure formation can be polished relative to the adjacent and elevated silicon nitride.

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